

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 245724US2X		SERIAL NO. 10/217,718 New Application	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Yasutaka NISHIOKA, et al.			
				FILING DATE Herewith		GROUP 3729	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
CJA	AO	2000-269326	9/29/00	Japan (with English Extract)		X	
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
CJA	AW	S. M. JANG, et al., "INTEGRATION OF CU AND LOW-K MATERIAL FOR DUAL-DAMASCENE PROCESS", Semiconductor Technology, (ISTC 2001), Vol. I, Pages 485-493					
CJA	AX	K. HIGASHI, et al., "A MANUFACTURABLE COPPER/LOW-K SiOC/SiCN PROCESS TECHNOLOGY FOR 90NM-NODE HIGH PERFORMANCE eDRAM", Proceedings of the 2002 International Interconnect Technology Conference, Pages 15-17					
CJA	AY	M. FAYOLLE, et al., "INTEGRATION OF Cu/SiOC IN DUAL DAMASCENE INTERCONNECT FOR 0.1µm TECHNOLOGY USING A NEW SiC MATERIAL AS DIELECTRIC BARRIER", Proceedings of the 2002 International Interconnect Technology Conference, Pages 39-41					
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner Carol J. Arbes					Date Considered 3/4/05		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							